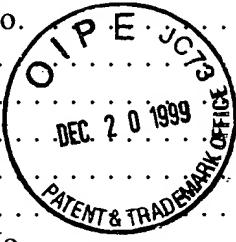


#6/Amndt B  
12/28/99  
C. McKinney

1 IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2 Application Serial No. .... 09/059,644  
3 Filing Date ..... April 13, 1998  
4 Inventor ..... Pai-Hung Pan  
5 Assignee ..... Micron Technology, Inc.  
6 Group Art Unit ..... 2822  
7 Examiner ..... M. Trinh  
8 Attorney's Docket No. .... MI22-898  
9 Title: Semiconductor Processing Methods Of Forming A Conductive Gate and Line



10 **RESPONSE TO SEPTEMBER 16, 1999 OFFICE ACTION**

11 To: Assistant Commissioner for Patents  
12 Washington, D.C. 20231  
13 From: Mark S. Matkin (Tel. 509-624-4276; Fax 509-838-3424)  
14 Wells, St. John, Roberts, Gregory & Matkin P.S.  
15 601 W. First Avenue, Suite 1300  
16 Spokane, WA 99201-3828

17 Sir:

18 Responsive to the Office Action dated September 16, 1999,  
19 Applicant amends and remarks as follows [unless otherwise indicated,  
20 deletions are bracketed, additions are underlined]:

21 **AMENDMENTS**

22 **In the Claims**

23 In Claim 43, at line 2, insert --layer-- after the phrase "overlying  
24 metal".

25 In Claim 46, at line 1, replace "said" with --the--.

26 In Claim 51, at line 4, replace "anisotropically" with  
27 --anisotropically--.

B